

# P-Channel 20 V (D-S) MOSFET

## PRODUCT SUMMARY

V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) Max.	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
- 20	0.0036 at V <sub>GS</sub> = - 10 V	- 40 <sup>e</sup>	72 nC
	0.0048 at V <sub>GS</sub> = - 4.5 V	- 40 <sup>e</sup>	
	0.0090 at V <sub>GS</sub> = - 2.5 V	- 40 <sup>e</sup>	

## FEATURES

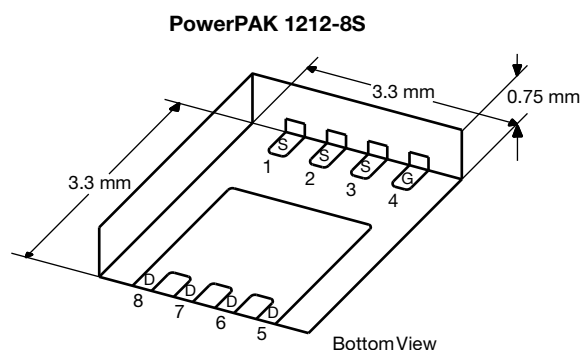
- TrenchFET<sup>®</sup> Power MOSFET
- Low Thermal Resistance PowerPAK<sup>®</sup> Package with Small Size and Low 0.75 mm Profile
- 100 % R<sub>g</sub> and UIS Tested
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

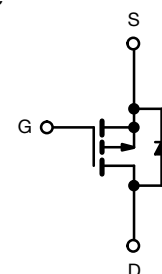
## APPLICATIONS

- Smart Phones, Tablet PCs, Mobile Computing
  - Battery Switch
  - Load Switch



### Ordering Information:

Si7655ADN-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

## ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	- 20	V
Gate-Source Voltage	V <sub>GS</sub>	± 12	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	A
		T <sub>C</sub> = 70 °C	
		T <sub>A</sub> = 25 °C	
		T <sub>A</sub> = 70 °C	
Pulsed Drain Current (t = 300 μs)	I <sub>DM</sub>	- 100	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	
Avalanche Current	I <sub>AS</sub>	- 20	mJ
Single-Pulse Avalanche Energy	E <sub>AS</sub>	20	
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	W
		T <sub>C</sub> = 70 °C	
		T <sub>A</sub> = 25 °C	
		T <sub>A</sub> = 70 °C	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 50 to 150	°C
Soldering Recommendations (Peak Temperature) <sup>c, d</sup>		260	

### Notes:

- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 1212-8S is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Package limited.

**THERMAL RESISTANCE RATINGS**

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, b</sup>	$t \leq 10$ s	$R_{thJA}$	21	26	°C/W
Maximum Junction-to-Case (Drain)	Steady State	$R_{thJC}$	1.7	2.2	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. Maximum under steady state conditions is 63 °C/W.

**SPECIFICATIONS** ( $T_J = 25$  °C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 20			V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = - 250 μA		- 12		mV/ °C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			2.6		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 0.5		- 1.1	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			- 1	μA
		V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ - 5 V, V <sub>GS</sub> = - 10 V	- 20			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 20 A		0.0030	0.0036	Ω
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 15 A		0.0039	0.0048	
		V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 10 A		0.0062	0.0090	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 20 A		90		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		6600		pF
Output Capacitance	C <sub>oss</sub>			890		
Reverse Transfer Capacitance	C <sub>rss</sub>			930		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 20 A		150	225	nC
				72	110	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 20 A		12		
Gate-Drain Charge	Q <sub>gd</sub>			19		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.5	2.6	5.2	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 10 V, R <sub>L</sub> = 1 Ω I <sub>D</sub> ≅ - 10 A, V <sub>GEN</sub> = - 4.5 V, R <sub>g</sub> = 1 Ω		45	90	ns
Rise Time	t <sub>r</sub>			45	90	
Turn-Off DelayTime	t <sub>d(off)</sub>			100	200	
Fall Time	t <sub>f</sub>			35	70	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 10 V, R <sub>L</sub> = 1 Ω I <sub>D</sub> ≅ - 10 A, V <sub>GEN</sub> = - 10 V, R <sub>g</sub> = 1 Ω		13	25	
Rise Time	t <sub>r</sub>			10	20	
Turn-Off DelayTime	t <sub>d(off)</sub>			110	220	
Fall Time	t <sub>f</sub>			25	50	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 40 <sup>c</sup>	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				- 100	
Body Diode Voltage	V <sub>SD</sub>	I <sub>F</sub> = - 10 A		- 0.75	- 1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C		30	60	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			17	26	nC
Reverse Recovery Fall Time	t <sub>a</sub>			15		ns
Reverse Recovery Rise Time	t <sub>b</sub>			15		

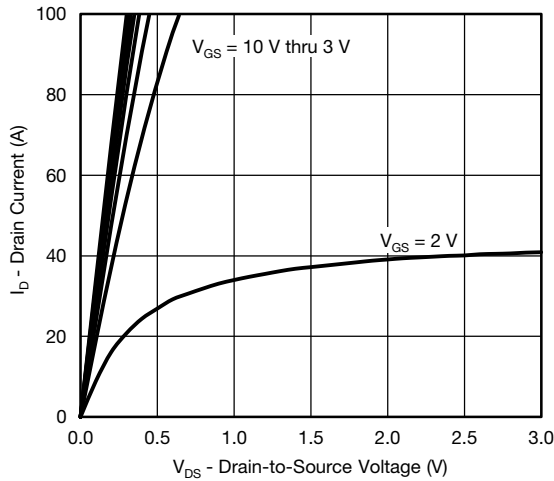
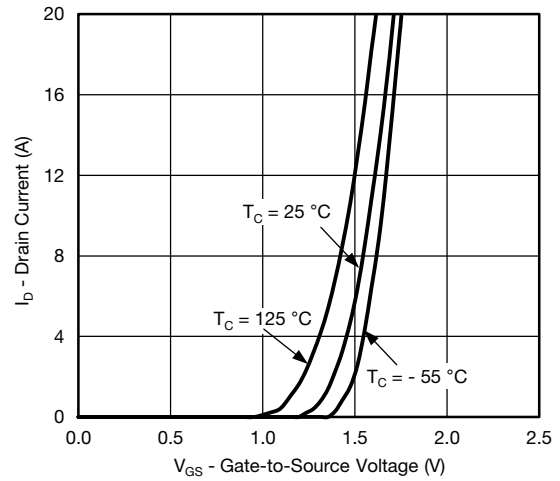
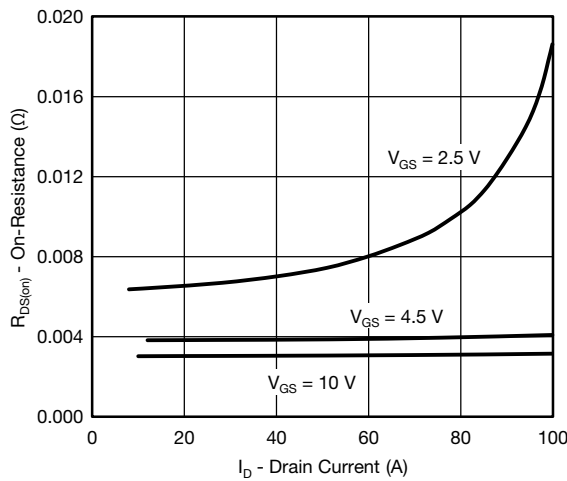
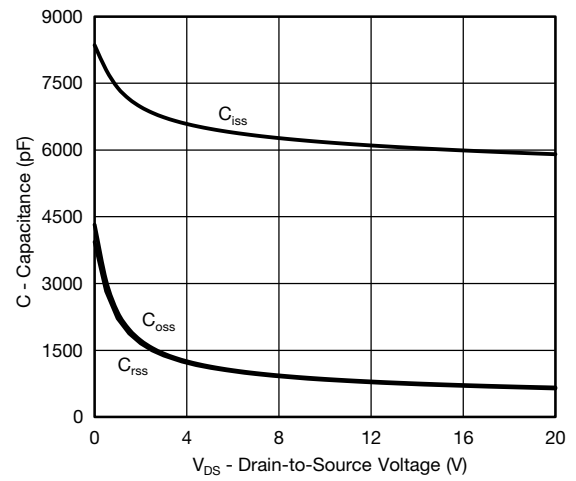
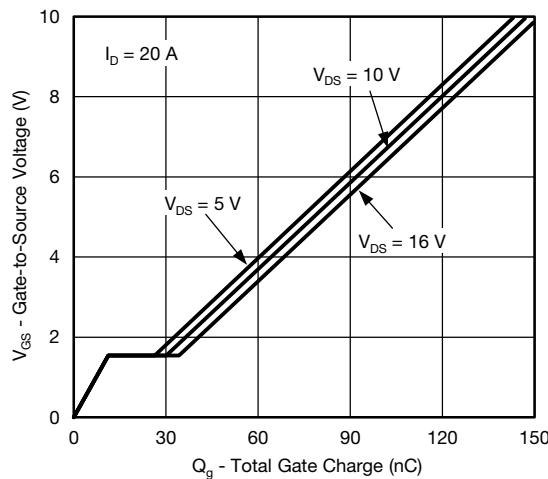
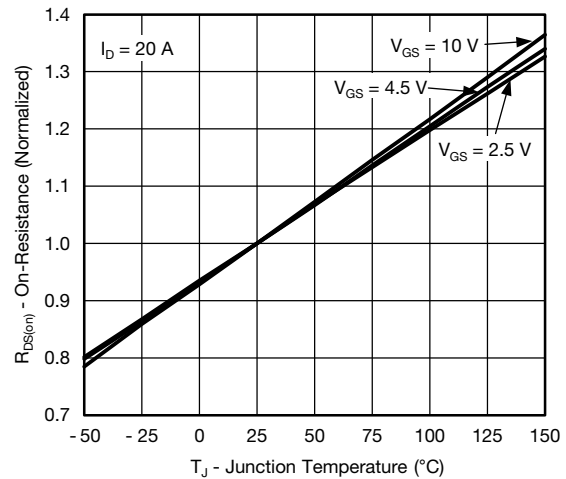
Notes:

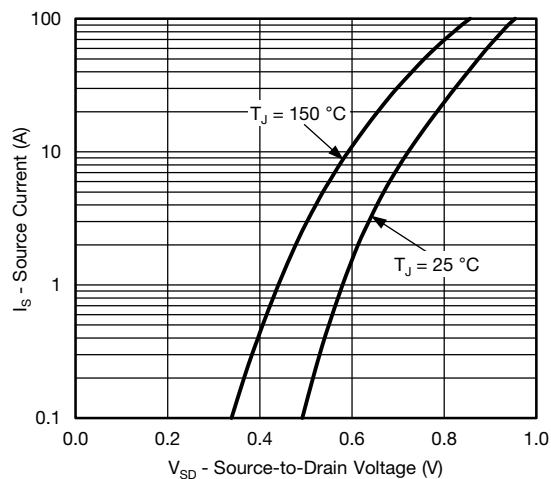
a. Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %.

b. Guaranteed by design, not subject to production testing.

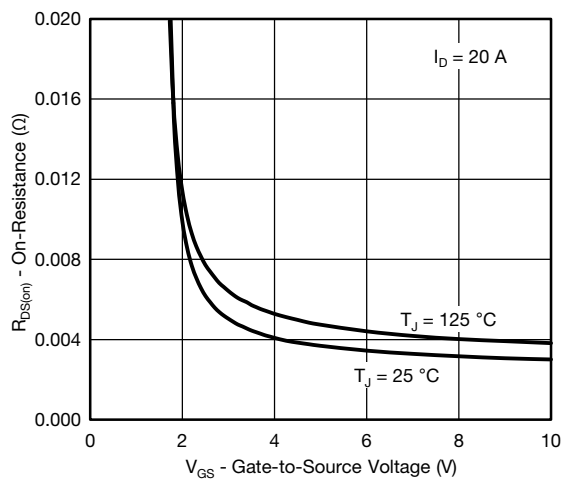
c. Package limited.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

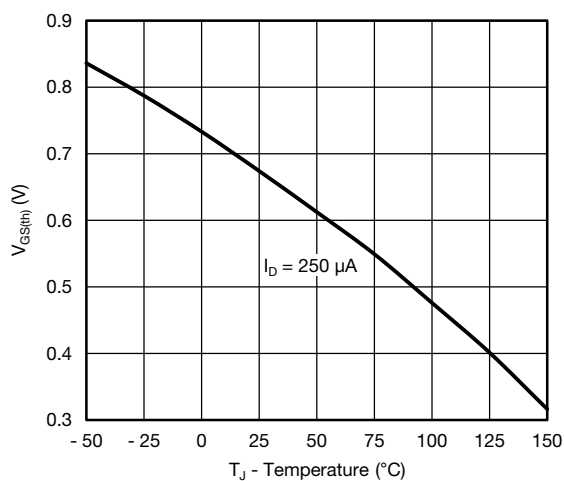
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current and Gate Voltage**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

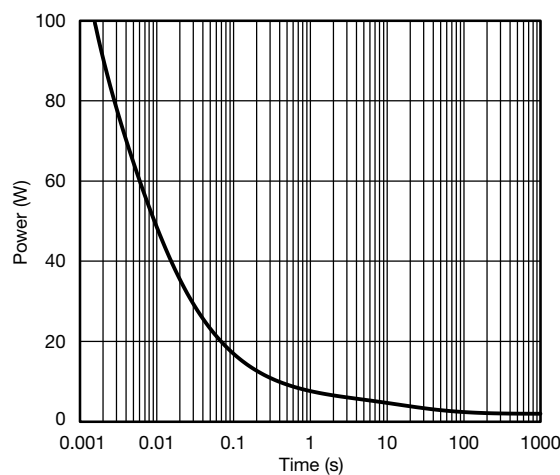
Source-Drain Diode Forward Voltage



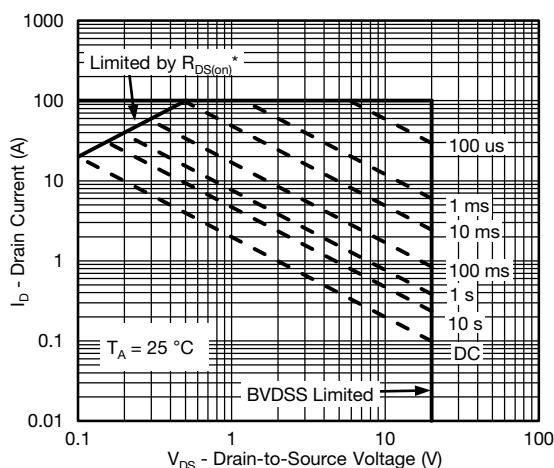
On-Resistance vs. Gate-to-Source Voltage



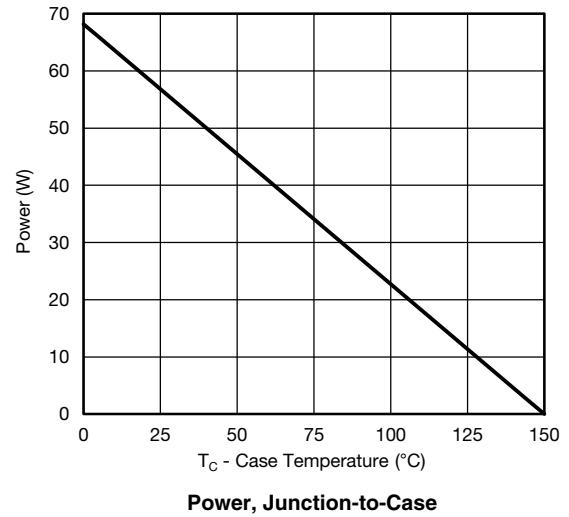
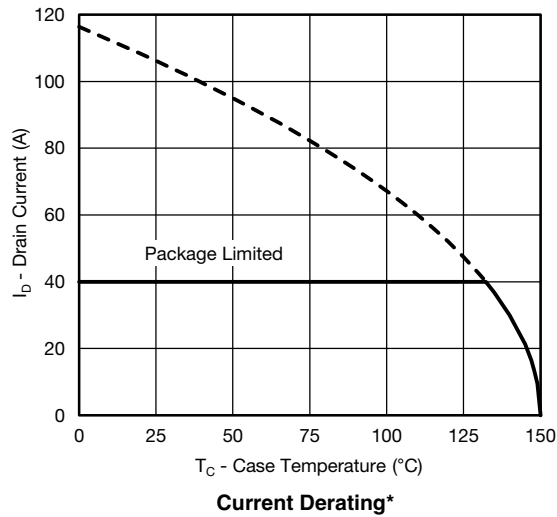
Threshold Voltage



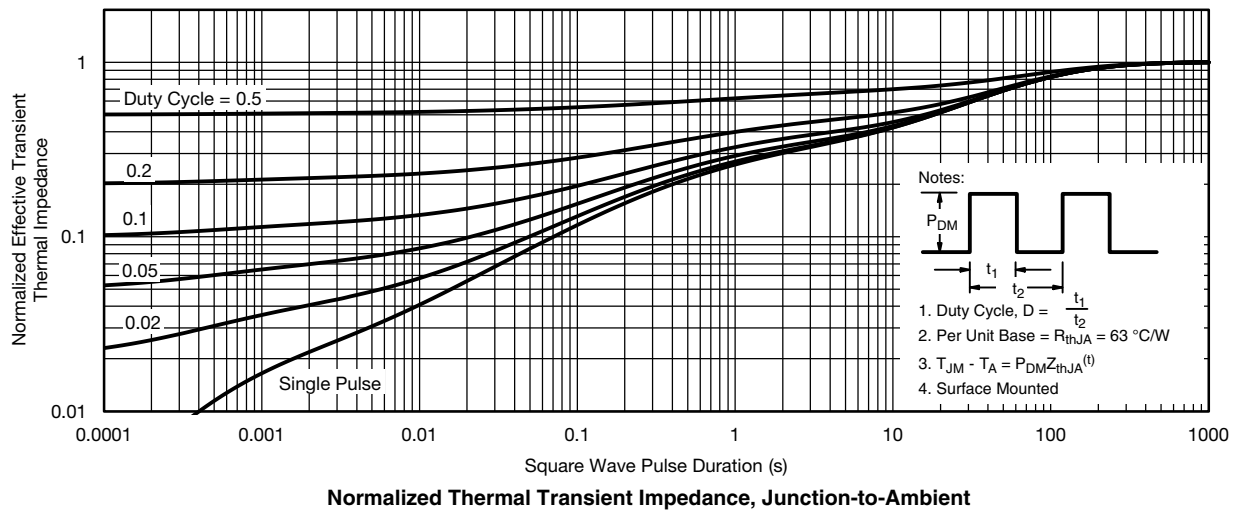
Single Pulse Power, Junction-to-Ambient

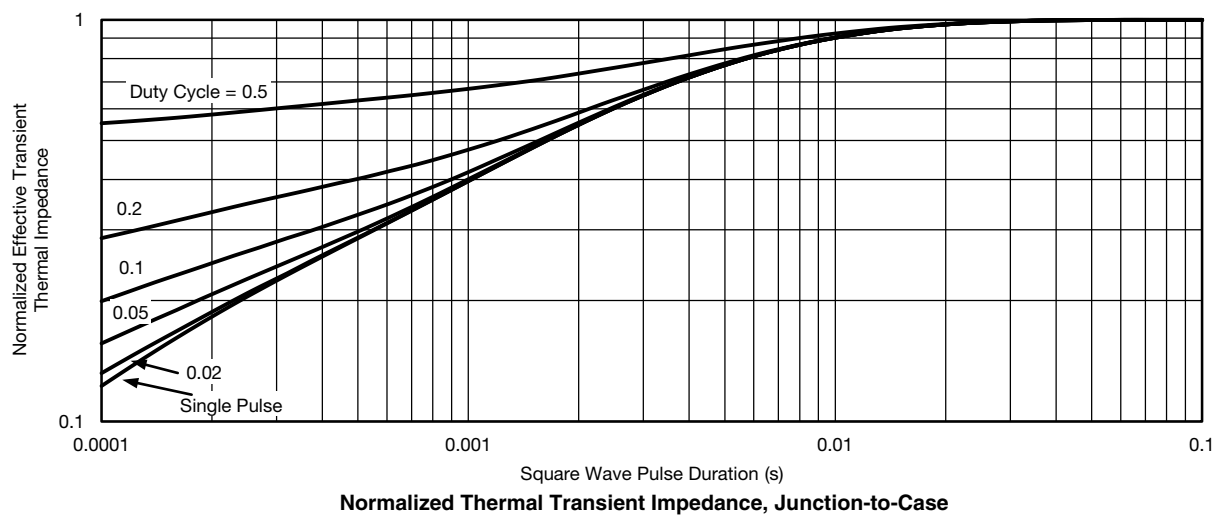
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area, Junction-to-Ambient

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


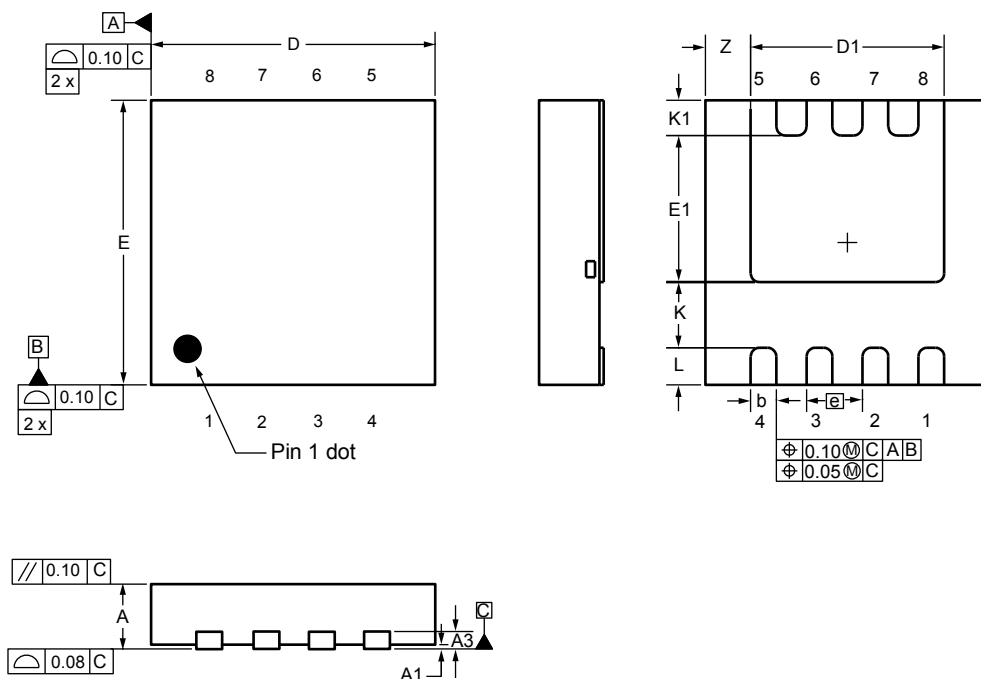
\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?62909](http://www.vishay.com/ppg?62909).

## Case Outline for PowerPAK® 1212-8S



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.67	0.75	0.83	0.026	0.030	0.033
A1	0.00	-	0.05	0.000	-	0.002
A3	0.20 ref.			0.008 ref		
b	0.25	0.30	0.35	0.010	0.012	0.014
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.15	2.25	2.35	0.085	0.089	0.093
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	1.60	1.70	1.80	0.063	0.067	0.071
e	0.65 bsc.			0.026 bsc.		
K	0.76 ref.			0.030 ref.		
K1	0.41 ref.			0.016 ref.		
L	0.33	0.43	0.53	0.013	0.017	0.021
Z	0.525 ref.			0.021 ref.		
ECN: C20-0862-Rev. B, 20-Jul-2020						
DWG: 6008						

## RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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